Product Preview

Low-Voltage 1.8/2.5/3.3V 8-Bit Transceiver

(3-State, Non-Inverting with Bushold)

The 74VCXH245 is an advanced performance, non-inverting 8-bit transceiver. It is designed for very high-speed, very low-power operation in 1.8 V, 2.5 V or 3.3 V systems.

The VCXH245 is designed as a byte control. The Transmit/Receive $(T/\overline{R}n)$ inputs determine the direction of data flow through the bi-directional transceiver. Transmit (active-HIGH) enables data from A ports to B ports; Receive (active-LOW) enables data from B to A ports. The Output Enable input (\overline{OE}) , when HIGH, disables both A and B ports by placing them in a HIGH Z condition. The data inputs include active bushold circuitry, eliminating the need for external pull-up resistors to hold unused or floating inputs at a valid logic state.

• Designed for Low Voltage Operation: $V_{CC} = 1.65-3.6 \text{ V}$

• High Speed Operation: 3.5 ns max for 3.0 to 3.6 V

4.2 ns max for 2.3 to 2.7 V 8.4 ns max for 1.65 to 1.95 V

• Static Drive: ±24 mA Drive at 3.0 V

±18 mA Drive at 2.3 V ±6 mA Drive at 1.65 V

- Includes Active Bushold to Hold Unused or Floating Data Inputs at a Valid Logic State
- Near Zero Static Supply Current in All Three Logic States (20 μA)
 Substantially Reduces System Power Requirements
- Latchup Performance Exceeds ±250 mA @ 85°C
- ESD Performance: Human Body Model >2000 V; Machine Model >200 V



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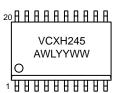
MARKING DIAGRAMS

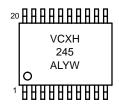


SO-20 DW SUFFIX CASE 751D



TSSOP-20 DT SUFFIX CASE 948E





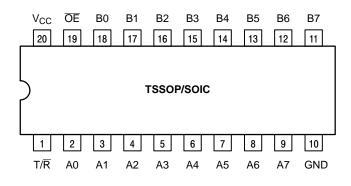


DQFN SUFFIX TBD CASE TBD 74VCXH245 AWLYYWW

A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week

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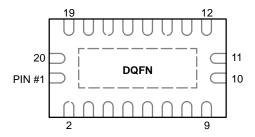


Figure 1. Pinout (Top View)

PIN NAMES

PINS	FUNCTION
OE	Output Enable Input
T/R	Transmit/Receive Input
A0-A7	Side A Bushold Inputs or 3-State Outputs
B0-B7	Side B Bushold Inputs or 3-State Outputs

TRUTH TABLE

INF	PUTS	OPERATING MODE	
ŌĒ	T/R	Non-Inverting	
L	L	B Data to A Bus	
L	Н	A Data to B Bus	
Н	Х	Z State	

H = High Voltage Level

L = Low Voltage Level Z = High Impedance State

X = High or Low Voltage Level and Transitions are Acceptable

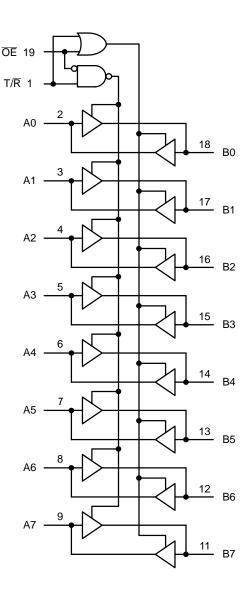


Figure 2. Logic Diagram

ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to + 4.6		V
VI	DC Input Voltage	$-0.5 \le V_{I} \le V_{CC} + 0.5$		V
Vo	DC Output Voltage	$-0.5 \le V_{O} \le V_{CC} + 0.5$	Note 1	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
lok	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
Io	DC Output Source/Sink Current	±50		mA
Icc	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

^{*} Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Min	Тур	Max	Unit
V _{CC}	Supply Voltage	Operating ata Retention Only	1.65 1.2	3.3 3.3	3.6 3.6	V
VI	Input Voltage		-0.3		V _{CC}	V
Vo	Output Voltage		0		V _{CC}	V
I _{OH}	HIGH Level Output Current, V _{CC} = 3.0 V - 3.6 V				-24	mA
I _{OL}	LOW Level Output Current, V _{CC} = 3.0 V - 3.6 V				24	mA
I _{OH}	HIGH Level Output Current, V _{CC} = 2.3 V - 2.7 V				-18	mA
I _{OL}	LOW Level Output Current, V _{CC} = 2.3 V - 2.7 V				18	mA
I _{OH}	HIGH Level Output Current, V _{CC} = 1.65 V - 1.95 V				-6	mA
I _{OL}	LOW Level Output Current, V _{CC} = 1.65 V - 1.95 V				6	mA
T _A	Operating Free-Air Temperature		-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V _{IN} from 0.8 V to 2.0	V, V _{CC} = 3.0 V	0		10	ns/V

^{**}Floating or unused control inputs must be held HIGH or LOW.

^{1.} I_O absolute maximum rating must be observed.

DC ELECTRICAL CHARACTERISTICS

			$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		
Symbol	Characteristic	Condition	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage (Note 2)	1.65 V ≤ V _{CC} < 1.95 V	0.65 x V _{CC}		V
		2.3 V ≤ V _{CC} ≤ 2.7 V	1.6		
		2.7 V < V _{CC} ≤ 3.6 V	2.0		
V _{IL}	LOW Level Input Voltage (Note 2)	1.65 V ≤ V _{CC} < 1.95 V		0.35 x V _{CC}	V
		2.3 V ≤ V _{CC} ≤ 2.7 V		0.7	
		2.7 V < V _{CC} ≤ 3.6 V		0.8	
V _{OH}	HIGH Level Output Voltage	1.65 V ≤ V_{CC} ≤ 3.6 V; I_{OH} = -100 μA	V _{CC} - 0.2		V
		V _{CC} = 1.65 V; I _{OH} = -6 mA	1.25		
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -6 \text{ mA}$	2.0		
		V _{CC} = 2.3 V; I _{OH} = -12 mA	1.8		
		V _{CC} = 2.3 V; I _{OH} = -18 mA	1.7		
		V _{CC} = 2.7 V; I _{OH} = -12 mA	2.2		
		V _{CC} = 3.0 V; I _{OH} = -18 mA	2.4		
		V _{CC} = 3.0 V; I _{OH} = -24 mA	2.2		
V _{OL}	LOW Level Output Voltage	$1.65 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		V _{CC} = 1.65 V; I _{OL} = 6 mA		0.3	
		V _{CC} = 2.3 V; I _{OL} = 12 mA		0.4	
		V _{CC} = 2.3 V; I _{OL} = 18 mA		0.6	
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 18 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	
I _I	Input Leakage Current	$V_{IN} = V_{CC}$ or GND; $V_{CC} = 3.6 \text{ V}$		±5.0	μΑ
I _{I(HOLD)}	Minimum Bushold Input Current	V _{CC} = 3.0 V, V _{IN} = 0.8 V	75		μΑ
		V _{CC} = 3.0 V, V _{IN} = 2.0 V	-75		
		V _{CC} = 2.3 V, V _{IN} = 0.7 V	45		
		V _{CC} = 2.3 V, V _{IN} = 1.6 V	-45		
		V _{CC} = 1.65 V, V _{IN} = 0.57 V	25		
		V _{CC} = 1.65 V, V _{IN} = 1.07 V	-25		
I _{I(OD)}	Minimum Bushold Over-Drive	V _{CC} = 3.6 V, (Note 3)	450		μΑ
	Current Needed to Change State	V _{CC} = 3.6 V, (Note 4)	-450		
		V _{CC} = 2.7 V, (Note 3)	300		
		V _{CC} = 2.7 V, (Note 4)	-300		
		V _{CC} = 1.95 V, (Note 3)	200		
		V _{CC} = 1.95 V, (Note 4)	-200		
I _{OZ}	3-State Output Current	$V_O = V_{CC}$ or GND; $V_{CC} = 3.6 \text{ V}$; $V_I = V_{IH}$ or V_{IL}		±10	μΑ
I _{CC}	Quiescent Supply Current (Note 5)	$1.65 \text{ V} \le \text{V}_{\text{CC}} \le 3.6 \text{ V}; \text{ V}_{\text{I}} = \text{GND or V}_{\text{CC}}$		20	μΑ
ΔI_{CC}	Increase in I _{CC} per Input	$2.7 \text{ V} < \text{V}_{CC} \le 3.6 \text{ V}; \text{V}_{IH} = \text{V}_{CC} - 0.6 \text{ V}$		750	μΑ

These values of V_I are used to test DC electrical characteristics only.
 An external driver must source at least the specified current to switch from LOW-to-HIGH.
 An external driver must sink at least the specified current to switch from HIGH-to-LOW.
 Outputs disabled or 3-state only.

AC CHARACTERISTICS (Note 6; $t_R = t_F = 2.0 \text{ ns}$; $C_L = 30 \text{ pF}$; $R_L = 500 \Omega$)

				Limits					
					T _A = -40°	C to +85°C			
			V _{CC} = 3.0	V to 3.6 V	V _{CC} = 2.3	V to 2.7 V	V _{CC} = 1.6	5 V to1.95 V	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} t _{PHL}	Propagation Delay Input to Output	1	0.6 0.6	3.5 3.5	0.8 0.8	4.2 4.2	1.5 1.5	8.4 8.4	ns
t _{PZH} t _{PZL}	Output Enable Time to High and Low Level	2	0.6 0.6	4.5 4.5	0.8 0.8	5.6 5.6	1.5 1.5	9.8 9.8	ns
t _{PHZ}	Output Disable Time From High and Low Level	2	0.6 0.6	3.6 3.6	0.8 0.8	4.0 4.0	1.5 1.5	7.2 7.2	ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 7)			0.5 0.5		0.5 0.5		0.75 0.75	ns

^{6.} For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C	
Symbol	Characteristic	Condition	Тур	Unit
V_{OLP}	Dynamic LOW Peak Voltage	$V_{CC} = 1.8 \text{ V}, \ C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	0.3	V
	(Note 8)	$V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	0.7	
		$V_{CC} = 3.3 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	1.0	
V_{OLV}	Dynamic LOW Valley Voltage	$V_{CC} = 1.8 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	-0.3	V
	(Note 8)	$V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	-0.7	
		$V_{CC} = 3.3 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	-1.0	
V_{OHV}	Dynamic HIGH Valley Voltage	$V_{CC} = 1.8 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	1.3	V
	(Note 9)	$V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	1.7	
		$V_{CC} = 3.3 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0 \text{ V}$	2.0	7

^{8.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

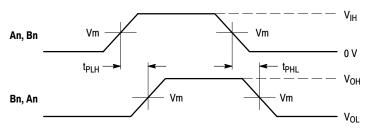
CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	Note 10	6	pF
C _{OUT}	Output Capacitance	Note 10	7	pF
C _{PD}	Power Dissipation Capacitance	Note 10, 10 MHz	20	pF

10. V_{CC} = 1.8, 2.5 or 3.3 V; V_{I} = 0 V or V_{CC} .

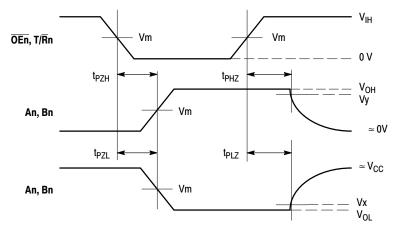
Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

^{9.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the HIGH state.



WAVEFORM 1 - PROPAGATION DELAYS

 t_R = t_F = 2.0 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns

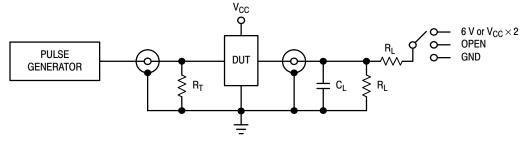


WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES

 $t_R = t_F = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$

Figure 3. AC Waveforms

	V _{CC}			
Symbol	3.3 V \pm 0.3 V	2.5 V \pm 0.2 V	1.8 V \pm 0.15 V	
V_{IH}	2.7 V	V _{CC}	V _{CC}	
V _m	1.5 V	V _{CC} /2	V _{CC} /2	
V_{x}	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V	
V _y	V _{OH} - 0.3 V	V _{OH} - 0.15 V	V _{OH} - 0.15 V	



TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	
t _{PZH} , t _{PHZ}	GND

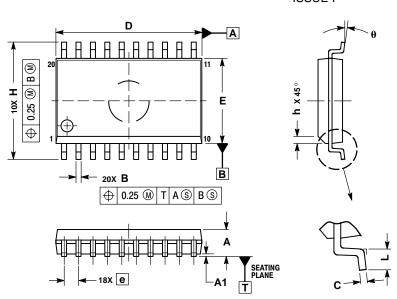
 C_L = 30 pF or equivalent (Includes jig and probe capacitance) R_L = 500 Ω or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

PACKAGE DIMENSIONS

SO-20 DW SUFFIX CASE 751D-05 ISSUE F



20X K REF

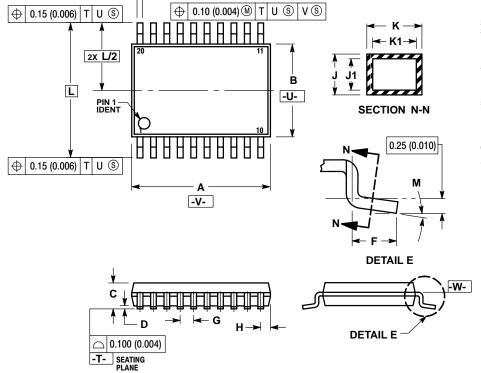
NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
- INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.

- PEH ASME Y14-MJ, 1994.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD
 PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0 °	7 °		

TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE A**



NOTES:

- OTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.066) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR
- (0.010) PER SIDE.

 5 DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .008 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

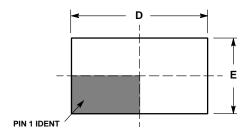
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252	BSC
М	0°	8°	0°	8°

PACKAGE DIMENSIONS

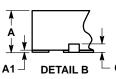
DQFN SUFFIX TBD CASE TBD **ISSUE O**

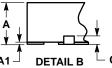


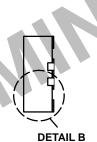
D₁

е

E1 20







- 1. CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSIONS A, D, AND E DO NOT INCLUDE
- MAXIMUM MOLD PROTRUSION 0.075 PER SIDE.

	MILLIMETERS	
DIM	MIN	MAX
Α	1.00 BSC	
A 1	0.00	0.05
b	0.18	0.30
С	0.20 BSC	
D	4.4	4.6
D1	2.85	3.15
Е	2.4	2.6
E1	0.85	1.15
е	0.5 BSC	
e1	3.5 BSC	
L	0.3	0.5

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